

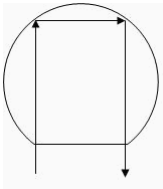
Part Number

Customer

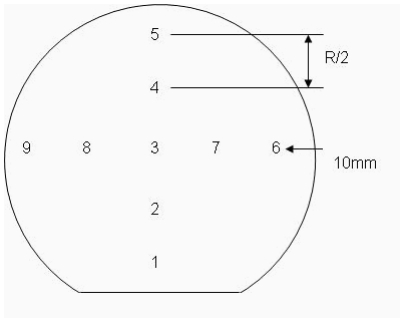
| Category | Parameter | Specification | Measurement Method |
|---------------|--|--|--------------------------------|
| OverallWafer | 1.0 Diameter | 100.00 +/- 0.20 mm | |
| | 2.0 Primary Flat Orientation | {110} +/- 1 degree | Customer supplied material |
| | 3.0 Primary Flat Length | 32.50 +/- 2.50 mm | Customer supplied material |
| | 4.0 Secondary Flat Orientation | none or SEMI Standard | Customer supplied material |
| | 5.0 Overall Thickness | 411.00 +/- 6.00 µm | ADE, 100% |
| | 6.0 Total Thickness Variation (TTV) | <3.00µm | Guaranteed by Process |
| | 7.0 Bow | <60.00µm | ADE to ASTM F534, 100% |
| | 8.0 Warp | <60.00µm | ADE to ASTM F534, 100% |
| | 9.0 Edge Chips | 0 | Bright Light, 100% |
| | 10.0 Edge Exclusion | 5mm | |
| HandleSilicon | 11.0 Handle Growth Method | CZ | Customer supplied material |
| | 12.0 Handle Orientation | {100} +/- 0.5 degree | Customer supplied material |
| | 13.0 Handle Thickness | 400.00 +/- 5.00 µm | ADE, 100% |
| | 14.0 Handle Doping Type | P | Customer supplied material |
| | 15.0 Handle Dopant | Boron | Customer supplied material |
| | 16.0 Handle Resistivity | 0.01-0.05 Ohm-cm | Customer supplied material |
| | 17.0 Backside Finish | Polished with oxide and lasermark (no scratches) | Guaranteed by process |
| BuriedOxide | 18.0 Oxide Type | Thermal | |
| | 19.0 Oxide Thickness | 10,000.00 +/- 500.00 A | Nanospec centre point, 4% |
| | 20.0 Oxide formed on | Device and/or Handle | |
| DeviceSilicon | 21.0 Device Growth Method | CZ | Customer supplied material |
| | 22.0 Device Orientation | {100} +/- 0.5 degree | Customer supplied material |
| | 23.0 Nominal Thickness | 10.00 +/- 0.80 µm | ADE single point, 100% (note3) |
| | 24.0 Distance to device silicon edge from wafer edge | < 2mm | Typical by Process |
| | 25.0 Device Doping Type | P | Customer supplied material |
| | 26.0 Device Dopant | Boron | Customer supplied material |
| | 27.0 Device Resistivity | <0.0015 Ohm-cm | Customer supplied material |
| | 28.0 Surface Voids | None | Bright Light, 100% (note2) |
| | 29.0 Haze | None | Bright Light, 100% (note2) |
| | 30.0 Scratches | None on both sides | Bright Light, 100% (note2) |

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|------------------|-------------------|---|---|
| Shipping Details | Wafer per box : | Max 25 |  |
| | Packaging : | Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging | |
| | Lot Shipment Data | Device Thickness Bow / Warp Data Handle and SOI Thickness | |

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|-------------------|---|--|--|
| Explanatory Notes | 1. Microscope inspection performed using microscope scan as below. 5x objective. | | |
| | 2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523. | | |
| | 3. 9 point measurement are as shown in the diagram below: | | |



Additional Information